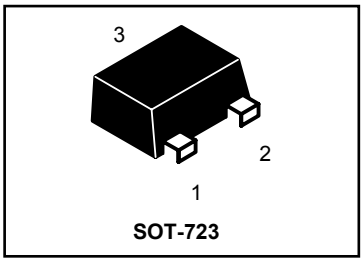
Small Signal MOSFET
115 mAmps, 60 Volts
N–Channel SOT–723

- Pb−Free Package is Available.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SOT-723

ORDERING INFORMATION

Device	Marking	Shipping
HM7002JR	72	8000 Tape & Reel

MAXIMUM RATINGS

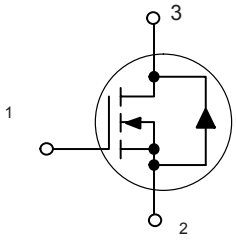
Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	60	Vdc
Drain–Gate Voltage (R_{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Drain Current – Continuous T_C = 25°C (Note 1.) – Pulse t < 10us	 I_D I_{DM}	 ±115 ±800	mAdc
Gate–Source Voltage – Continuous	V_{GS}	±20	Vdc

THERMAL CHARACTERISTICS

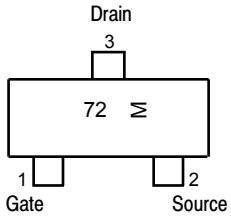
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 2.) T_A = 25°C Derate above 25°C	P_D	150 1.2	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. FR–5 = 1.0 x 0.75 x 0.062 in.
3. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

N - Channel



MARKING DIAGRAM & PIN ASSIGNMENT



72 = Device Code
M = Month Code

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μAdc)		$V_{(BR)DSS}$	60	–	–	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 60 Vdc)	T_J = 25°C T_J = 125°C	I_{DSS}	– –	– –	1.0 500	μAdc
Gate–Body Leakage Current, Forward (V_{GS} = 20 Vdc)		I_{GSSF}	–	–	100	nAdc
Gate–Body Leakage Current, Reverse (V_{GS} = – 20 Vdc)		I_{GSSR}	–	–	–100	nAdc
ON CHARACTERISTICS (Note 2.)						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc)		$V_{GS(th)}$	1.0	1.8	2.2	Vdc
On–State Drain Current (V_{DS} ≥ 2.0 $V_{DS(on)}$, V_{GS} = 10 Vdc)		$I_{D(on)}$	500	–	–	mA
Static Drain–Source On–State Voltage (V_{GS} = 10 Vdc, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc)		$V_{DS(on)}$	 – –	 – –	 3.75 0.375	Vdc
Static Drain–Source On–State Resistance (V_{GS} = 10 V, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc)		$r_{DS(on)}$	 – –	 – –	 4 4	Ohms
Forward Transconductance (V_{DS} ≥ 2.0 $V_{DS(on)}$, I_D = 200 mAdc)		g_{FS}	80	–	–	mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	–	17	50	pF
Output Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	–	10	25	pF
Reverse Transfer Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	–	2.5	5.0	pF
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = 25 Vdc , I_D ≅ 500 mAdc, R_G = 25 Ω, R_L = 50 Ω, V_{gen} = 10 V)	$t_{d(on)}$	–	7	20	ns
Turn–Off Delay Time		$t_{d(off)}$	–	11	40	ns
BODY–DRAIN DIODE RATINGS						
Diode Forward On–Voltage (I_S = 115 mAdc, V_{GS} = 0 V)		V_{SD}	–	–	–1.5	Vdc
Source Current Continuous (Body Diode)		I_S	–	–	–115	mAdc
Source Current Pulsed		I_{SM}	–	–	–800	mAdc

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

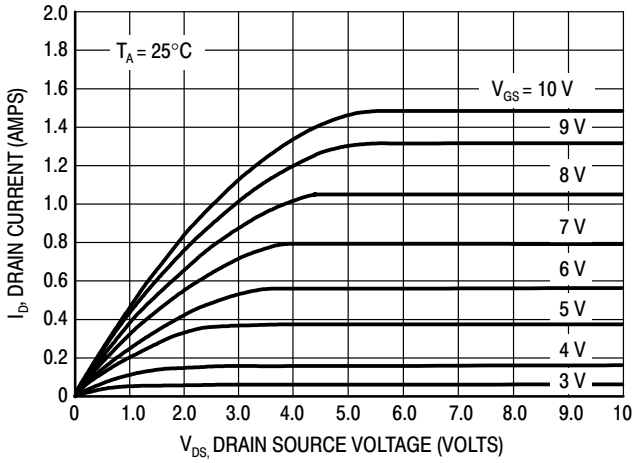


Figure 1. Ohmic Region

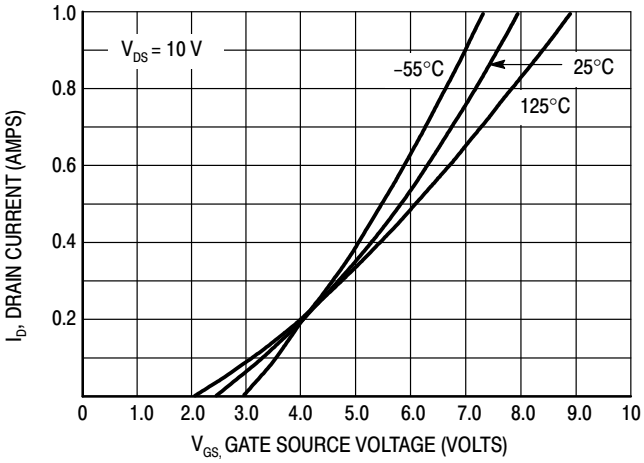


Figure 2. Transfer Characteristics

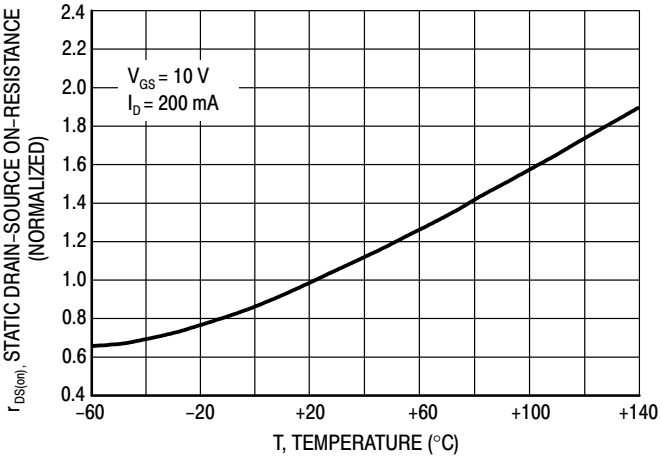


Figure 3. Temperature versus Static Drain–Source On–Resistance

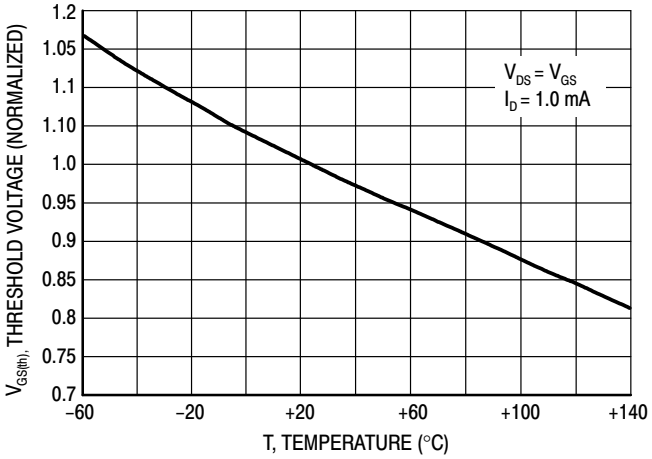


Figure 4. Temperature versus Gate Threshold Voltage

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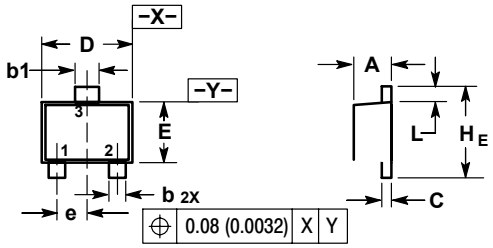
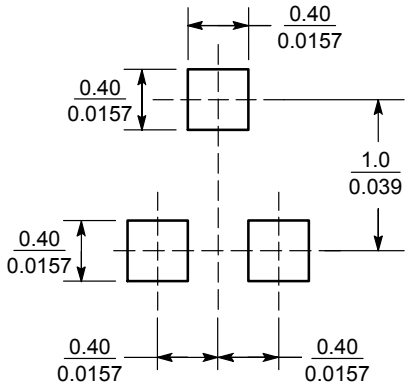


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.20	0.27	0.0059	0.0079	0.0106
b1	0.25	0.3	0.35	0.010	0.012	0.014
C	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
e	0.40 BSC			0.016 BSC		
H E	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

SOLDERING FOOTPRINT



(mm / inches)